

GLOSSARY

R_b:

Resistance through the bulk material.

R_g:

Resistance to ground.

R_s:

Surface resistance

R_v:

Volume resistance

Ω:

Ohm

A-Static:

Former name of low charging material.

Antistatic:

First name of low charging material. Still used in common language (much more than the replacement “A-static”).

CBM:

Charged Board Model.

CDM:

Charged Device Model.

Conductive:

See electrostatic conductive.

Dissipative:

See electrostatic dissipative.

ECU:

Electronic Controller Unit.

Electrostatic conductive:

Packaging with a surface resistance between $1 \times 10^2 \Omega$ and $< 1 \times 10^5 \Omega$.

Electrostatic discharge (ESD):

Transfer of charge between bodies at different electrostatic potentials caused by direct contact or induced by electrostatic field.

Electrostatic discharge sensitive device (ESDS):

Discrete device, integrated circuit or assembly that may be damaged by electrostatic fields or electrostatic discharge encountered in routine handling, testing or transit

Electrostatic discharge shielding:

Barrier or enclosure that limits the passage of current and attenuates the energy resulting from an electrostatic discharge such that the maximum energy from 1 000 V human body model discharge is less than or equal to 50 nJ.

Electrostatic dissipative:

Packaging with a surface resistance $\geq 1 \times 10^5 \Omega$ and $< 1 \times 10^{11} \Omega$.

EOS:

Electrical Overstress

EPA:

See ESD protected area (EPA).

ESD:

See Electrostatic discharge.

ESD protected area (EPA):

Area in which ESDS can be handled with accepted risk of damage as a result of electrostatic discharge or fields.

ESDS:

See Electrostatic discharge sensitive device.

ESD sensitivity:

Maximum voltage at which the ESDS does not suffer any ESD damage.

FCDM:

Field induced Charged Device Model.

FFB:

Field From Board Model.

FIM:

Field Induced Model.

Ground:

Conducting mass of the earth whose electric potential at any point is conventionally taken at zero.

HBM:

Human Body Model.

Insulating:

Packaging with a surface resistance $\geq 1 \times 10^{11} \Omega$.

Intimate packaging:

Material which makes contact with ESDS.

k:

Kilo.

Low charging:

packaging exhibiting properties which minimize any charge generation.

MOSFET:

Metal-Oxide-Semiconductor Field Effect Transistor.

PPM:

Parts Per Million.

Proximity packaging:

Material not making contact with ESDS but which is used to enclose one or more devices.

Static:

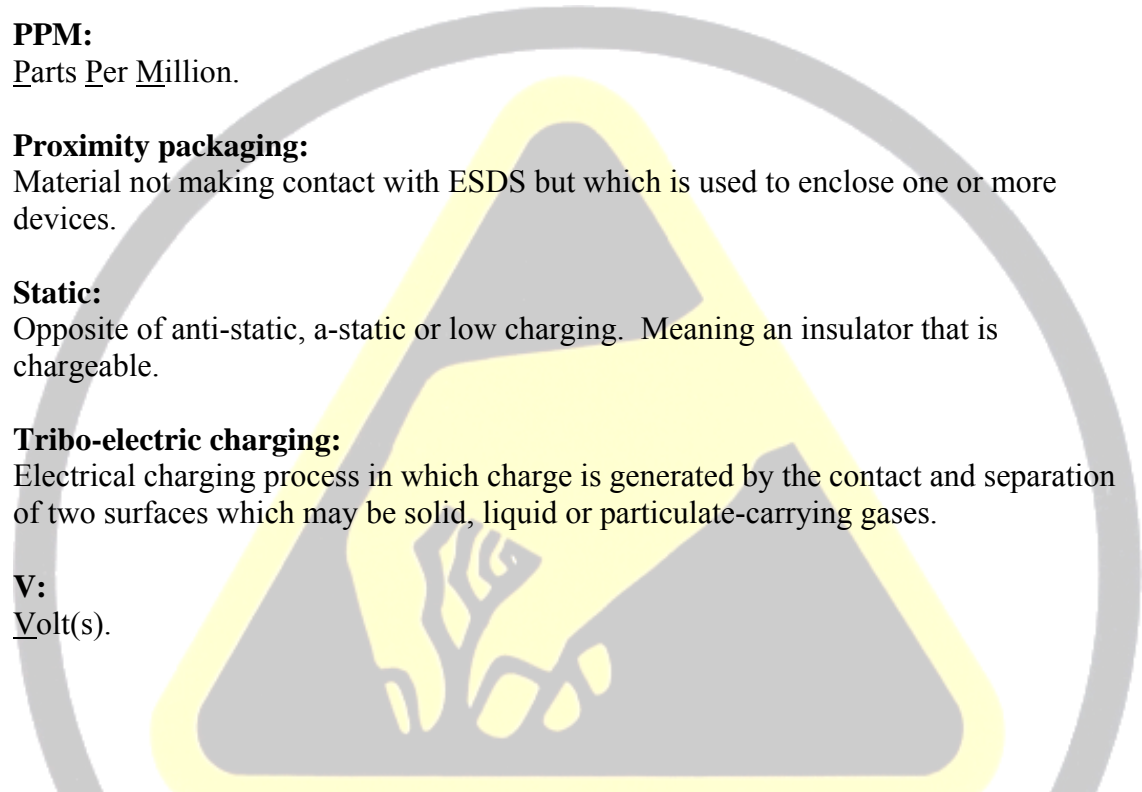
Opposite of anti-static, a-static or low charging. Meaning an insulator that is chargeable.

Tribo-electric charging:

Electrical charging process in which charge is generated by the contact and separation of two surfaces which may be solid, liquid or particulate-carrying gases.

V:

Volt(s).



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